etching PECVD oxide
using PT ICP
with ZEP520 mask
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9/17/2010
Process Flow

• 4” diam. 100 orientation silicon substrate
• PECVD oxide deposition
  • tool = Unaxis PECVD
  • recipe = std_ox
    • 900 mTorr, SiH4 400 sccm, N20 900 sccm, 25W @ 13.56MHz, T=250C
  • dep rate = rate ~578 A/min, t= 4min 20sec
  • thickness = 247 nm, Nanospec reflectometer
• ZEP520A coat
  • 3000 RPM, 1500 RPM/s, 60 sec
  • 180 C, hot plate bake, 2min
  • ~340 nm thickness, Dektak profilometer
  • break 4” wafer into pieces for further processing
• EBL exposure
  • tool = JBX-9300FS
  • 100kV, 15nA, aperture = 7
  • dose range = 220 – 260 uC/cm2 (for 200 nm squares on 300 nm pitch)
• Develop
  • 2 min immersion in amyl acetate
  • 30 sec immersion rinse in IPA
• Oxide Etch
  • pieces mounted on Si carrier wafer
  • tool = PT ICP
  • recipe = C4F8_OX
    • 5 mTorr, 28 sccm CO2, 15 sccm C4F8, 5 sccm Ar, 40 W RIE, 800 W ICP
  • etch time = 84 sec
  • observed DC bias = 162 V
Post develop, prior to etch
200 nm squares on 300 nm pitch
15 nA current, dose = 240 uC/cm²

ZEP520 resist thickness = \( \frac{306.5}{\sin(70)} \) = 326 nm
PECVD oxide thickness = \( \frac{218.9}{\sin(70)} \) = 233 nm
top dimension = 219 nm
bottom dimension = 250 nm
remaining ZEP520 resist = 89 / sin(70) = 95 nm
etched ZEP520 resist = 326 – 95 = 231 nm
resist etch rate = 231/84 = 2.8 nm/sec
remaining PECVD oxide = 41 / sin(70) = 44 nm
etched PECVD oxide = 233 – 44 = 189 nm
oxide etch rate = 189/84 = 2.3 nm/sec
selectivity = 2.3/2.8 = 0.8
oxide sidewall angle = 82 degrees
top dimension = 221 nm
bottom dimension = 175 nm
Large structure etch rate

- 50 x 50 um square structure on same sample as 200 nm squares is fully etched, demonstrating etch lag
- PECVD oxide etched = 215 / sin (70) = 229 nm
- oxide etch rate > 229 nm / 84 sec = 2.7 nm/sec
- ZEP520 amount etch = 326 – 118/sin(70) = 200 nm
- ZEP520 etch rate = 200 nm / 84 sec = 2.4 nm/sec
- selectivity > 2.7/2.4 = 1.1
- residue in etched area likely due to intentional underdosing of square leaving some resist residue
Summary

• large structure (50 x 50 um)
  • PECVD oxide etch rate > 2.7 nm/sec
  • ZEP520 etch rate = 2.4 nm/sec
  • selectivity = 1.1 oxide to resist

• 200 nm squares on 300 nm pitch
  • PECVD oxide etch rate = 2.3 nm/sec
  • ZEP520 etch rate = 2.8 nm/sec
  • selectivity = 0.8 oxide to resist
  • sidewall angle = 82 degrees